

SOT-23 Plastic-Encapsulated Diodes

MMBD914LT1 SWITCHING DIODE

FEATURES

Power dissipation

$$P_D: 225 \text{ mW (Tamb=25°C)}$$

Forward Current

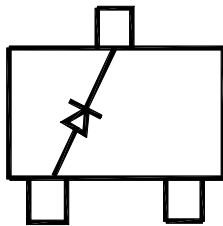
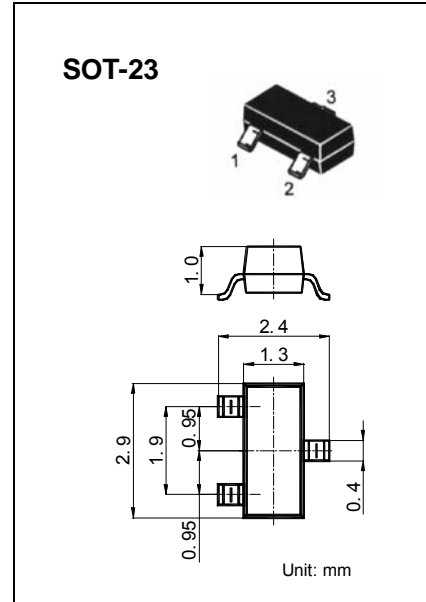
$$I_F: 200 \text{ mA}$$

Reverse Voltage

$$V_R: 75 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



Marking 5D

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R = 75\text{V}$		2.5	μA
Forward voltage	V_F	$I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0\text{V}, f = 1\text{MHz}$		20	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{mA}$ $V_R = 5\text{V}$ $R_C = 100\Omega$		4	nS